

In The Claims

Applicant submits below a complete listing of the current claims, with any insertions indicated by underlining and any deletions indicated by strikeouts and/or double bracketing.

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of the Claims

1. (Original) A vertical unipolar component formed in a semiconductor substrate, said component comprising junctions formed at the surface of parts of said substrate separated with insulated trenches extending in an upper portion of the substrate, in which the insulated trenches are filled with a vertical multiple-layer of at least two conductive elements separated by an insulating layer, the multiple-layer depth being, at most, equal to the thickness of said upper portion.

2. (Original) The component of claim 1, wherein the multiple-layer depth is equal to the thickness of the upper portion, the insulating layer also separating the elements of a substrate portion underlying the upper portion.

3. (Original) The component of claim 1, wherein at least part of the elements are conductive grains.

4. (Original) The component of claim 1, wherein at least part of the elements are blocks exhibiting, in top view, a same surface area as the multiple-layer.

5. (Original) The component of claim 1, forming a Schottky diode having its cathode corresponding to said upper portion.

Please cancel claims 6 and 7.

6. (Cancelled)

7. (Cancelled)

8. (New) A vertical unipolar component formed in a semiconductor substrate, the component comprising junctions formed at a surface of regions of the substrate separated by

insulated trenches extending in an upper portion of the substrate, wherein the insulated trenches contain at least two conductive elements separated by an insulating layer.

9. (New) The component of claim 8, wherein a depth of the at least two conductive elements separated by an insulating layer is, at most, equal to a thickness of the upper portion.

10. (New) The component of claim 8, wherein the insulating layer also separates elements of a substrate portion underlying the upper portion.

11. (New) The component of claim 8, wherein at least part of the elements are conductive grains.

12. (New) The component of claim 8, wherein at least part of the elements are blocks exhibiting, in top view, a same surface area as one of the trenches.

13. (New) The component of claim 8, forming a Schottky diode having its cathode corresponding to said upper portion.